

# 1S457

## High Speed Response OPIC Light Detector

### Features

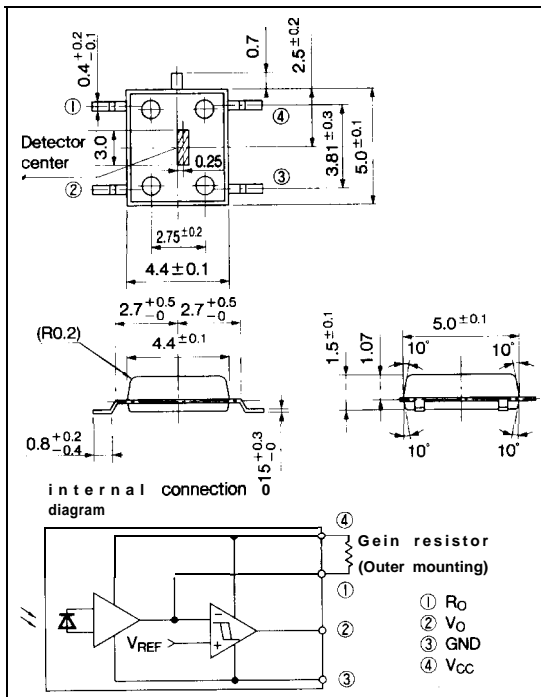
1. High speed response  
( $t_{PHL}$  : TYP. 300ns)
2. Uses a pattern to allow positional deviation of the semiconductor laser spot  
(Chip size: 0.5mm X3.0mm)
3. Open collector output
4. Capable of sensitivity adjustment due to external resistor

### Applications

1. Laser beam printers

### Outline Dimensions

(Unit : mm)

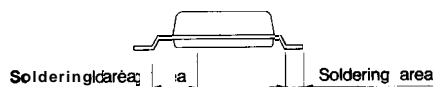


4  
OPIC Light Detectors

\*"OPIC" (Optical IC) is a trademark of the SHARP Corporation. An OPIC consists of a light-detecting element and signal processing circuit integrated onto a single chip.

### Absolute Maximum Ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Rating	Unit
*1 Supply voltage	V <sub>CC</sub>	-0.5 to +7	v
High level output voltage	V <sub>OH</sub>	7	v
Low level output current	I <sub>OL</sub>	40	mA
Operating temperature	T <sub>opr</sub>	-25 to +80	°C
Storage temperature	T <sub>stg</sub>	-40 to +85	°C
*2 Soldering temperature	T <sub>sol</sub>	260	°C
Power dissipation	P	150	mW
R <sub>o</sub> terminal power dissipation	p <sub>RO</sub>	24	mW
*3 Incident light intensity	PI	5	mW
*3 Radiant intensity	E <sub>e</sub>	60	W/cm <sup>2</sup>



- \*1 For 1 minute
- \*2 For 3 seconds at the position shown in the drawing
- \*3 Maximum allowable incident light intensity and radiant intensity of laser beam ( $\lambda = 780\text{nm}$ ) to the device.

**Electro-optical Characteristics**

( $V_{cc} = 5V, T_a = 25^\circ C$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
High level output current	$I_{OH}$	$R_O=51k\Omega, E_V=0lx$	—	—	100	$\mu A$	
Low level output voltage	$V_{OL}$	$I_{OL}=40mA, E_V=1\ 000lx$	—	0.35	0.52	v	
High level supply current	$I_{CCH}$	$R_O=51k\Omega, E_V=OIX$	—	3.0	6.5	mA	
Low level supply current	$I_{CCL}$	$R_O=51k\Omega, E_V=1\ 000lx$	—	5.8	8.6	mA	
Ro terminal OFF set current	$I_{OSRO}$	$R_O=5.1k\Omega$	—	8	15	$\mu A$	
*4 "High→Low" threshold illuminance 1	$E_{VHL1}$	$R_O=51k\Omega$	250	360	470	lx	
*4 "High→Low" threshold illuminance 2	$E_{VHL2}$	$R_O=5.1k\Omega$	—	4500	—	lx	
"High→Low" threshold incident light intensity	$P_{IHL}$	$R_O=5.1k\Omega, \lambda =780nm$	—	100	—	$\mu W$	
Response time	"High→Low" propagation delay time	$C_L=15pF, Duty=1:1$ $P_I=0.2mW, \lambda =780nm$ $R_O=5.1k\Omega, R_L=510\Omega$	$t_{PHL}$	—	300	500	ns
	"Low→High" propagation delay time		$t_{PLH}$	—	300	500	ns
	Rise time		$t_r$	—	100	500	ns
	Fall time		$t_f$	—	50	200	ns

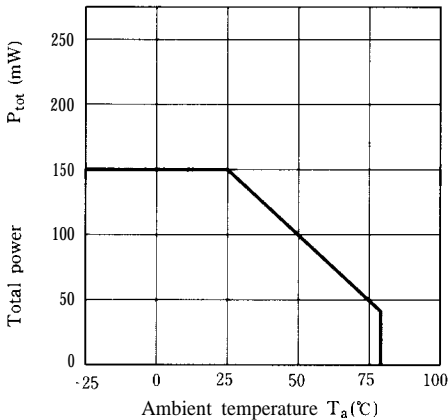
\*4  $E_V, E_{VHL}$  represent illuminance by CIE standard light source A (tungsten lamp).

**Recommended Operating Conditions**

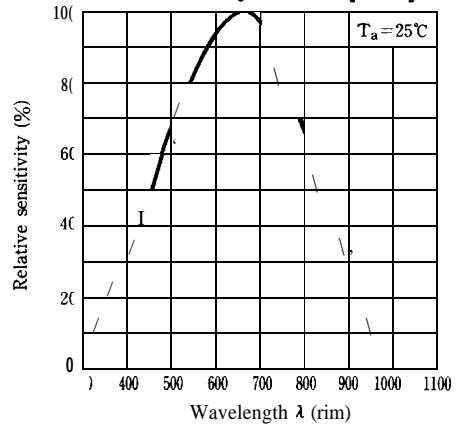
Parameter	Symbol	MIN.	MAX.	Unit
Operating supply voltage	$V_{cc}$	4.5	5.5	v
Operating temperature	$T_{opr}$	0	60	'c
Incident light intensity ( $\lambda = 780nm$ )	$P_I$	—	2.5	mW
Gain resistance	$R_O$	0.39	5.1	k $\Omega$

In order to stabilize power supply line, connect a by-pass capacitor of 0.1  $\mu F$  between  $V_{cc}$  and GND at the position of 1cm or less from lead pins.

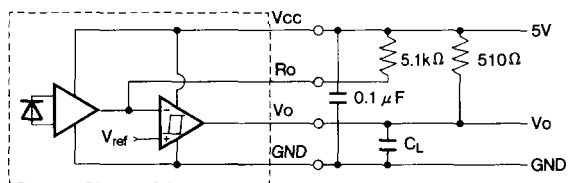
**Fig. 1 Total Power Dissipation vs. Ambient Temperature**



**Fig. 2 Spectral Sensitivity Ambient Temperature (TYP.)**

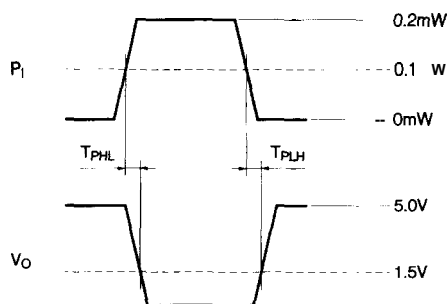


## Test Circuit for Response Time



Notes 1)  $C_L$  includes probe and wiring capacity.

2) Connect a by-pass ceramic capacitor of  $0.1 \mu\text{F}$  between  $V_{cc}$  and GND at the position within 1cm from lead pins.



● Please refer to the chapter "Precautions for Use" (Page 78 to 93)